

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-12 (Canceled).

13. (Currently amended) A method of manufacturing a semiconductor device comprising:

discharging a first composition containing a first photosensitizer on a first conductive layer to form a plurality of first resist patterns under reduced pressure;

exposing the plurality of first resist patterns by irradiation of light using a first photomask, the light having a photosensitive wavelength region of the first photosensitizer, wherein a first portion where the light is irradiated and a second portion where the light is not irradiated are formed in each of the plurality of first resist patterns;

removing one of the first portion and the second portion by developing the plurality of first resist patterns to form a plurality of second resist patterns;

etching the first conductive layer by using the plurality of second resist patterns as a mask to form a plurality of gate wirings and a plurality of gate electrodes over a substrate;

removing the plurality of second resist patterns on the first conductive layer;

forming an insulating film over the plurality of gate wirings and the plurality of gate electrodes;

forming a plurality of semiconductor islands over the plurality of gate electrodes with said insulating film interposed therebetween;

discharging a second composition containing a second photosensitizer on a second conductive layer to form a plurality of third resist patterns under reduced pressure;

exposing the plurality of third resist patterns by irradiation of light using a second photomask, the light having a photosensitive wavelength region of the second photosensitizer, wherein a third portion where the light is irradiated and a fourth portion where the light is not irradiated are formed in each of the plurality of third resist patterns;

removing one of the third portion and the fourth portion by developing the plurality of third resist patterns to form a plurality of fourth resist patterns;

etching the second conductive layer by using the plurality of fourth resist patterns as a mask to form a plurality of pixel electrodes arranged in a matrix form over the substrate;

removing the plurality of fourth resist patterns on the second conductive layer;

discharging a third composition containing a third photosensitizer on a third conductive layer to form a plurality of fifth resist patterns under reduced pressure;

exposing the plurality of fifth resist patterns by irradiation of light using a third photomask, the light having a photosensitive wavelength region of the third photosensitizer, wherein a fifth portion where the light is irradiated and a sixth portion where the light is not irradiated are formed in each of the plurality of fifth resist patterns;

removing one of the fifth portion and the sixth portion by developing the plurality of fifth resist patterns to form a plurality of sixth resist patterns;

etching the third conductive layer by using the plurality of sixth resist patterns as a mask to form a plurality of source wirings wherein said plurality of source wirings extend across said plurality of gate wirings; and

removing the plurality of sixth resist patterns on the third conductive layer.

14. (Currently Amended) A method of manufacturing a semiconductor device according to claim 13, wherein each of the first composition, the second composition, and the third composition containing the photosensitizer is made by dissolving or by dispersing one of the first photosensitizer, the second photosensitizer, and the third photosensitizer into a solvent.

15. (Previously Presented) A method of manufacturing a semiconductor device according to claim 13, wherein said semiconductor device is incorporated into at least one selected from the group consisting of a display device, a personal computer and a portable image reproduction device.

16. (Currently amended) A method of manufacturing a semiconductor device comprising:

discharging a first composition containing a first photosensitizer on a first conductive layer to form a plurality of first resist patterns under reduced pressure;

exposing the plurality of first resist patterns by irradiation of light using a first photomask, the light having a photosensitive wavelength region of the first photosensitizer, wherein a first portion where the light is irradiated and a second portion where the light is not irradiated are formed in each of the plurality of first resist patterns;

removing one of the first portion and the second portion by developing the plurality of first resist patterns to form a plurality of second resist patterns;

etching the first conductive layer by using the plurality of second resist patterns as a mask to form a plurality of gate wirings and a plurality of gate electrodes over a substrate;

photomask, the light having a photosensitive wavelength region of the third photosensitizer, wherein a fifth portion where the light is irradiated and a sixth portion where the light is not irradiated are formed in each of the plurality of fifth resist patterns;

removing one of the fifth portion and the sixth portion by developing the plurality of fifth resist patterns to form a plurality of sixth resist patterns;

etching the third conductive layer by using the plurality of sixth resist patterns as a mask to form a plurality of source wirings wherein said plurality of source wirings extend across said plurality of gate wirings; and

removing the plurality of sixth resist patterns on the third conductive layer.

17. (Currently Amended) A method of manufacturing a semiconductor device according to claim 16, wherein each of the first composition, the second composition, and the third composition containing the photosensitizer is made by dissolving or by dispersing one of the first photosensitizer, the second photosensitizer, and the third photosensitizer into a solvent.

18. (Previously Presented) A method of manufacturing a semiconductor device according to claim 16, wherein said semiconductor device is incorporated into at least one selected from the group consisting of a display device, a personal computer and a portable image reproduction device.

19. (Previously Presented) A method for manufacturing a semiconductor device comprising the steps of:

discharging a composition on an object to form a plurality of first resist patterns under reduced pressure, the composition containing a photosensitizer;

removing the plurality of second resist patterns on the first conductive layer;

forming an insulating film over the plurality of gate wirings and the plurality of gate electrodes;

forming a plurality of first semiconductor islands over the plurality of gate electrodes with said insulating film interposed therebetween;

forming each of a plurality of channel protective layers over each of the plurality of first semiconductor islands;

forming a plurality of second semiconductor islands over the plurality of first semiconductor islands with the plurality of channel protective layers interposed therebetween;

discharging a second composition containing a second photosensitizer on a second conductive layer to form a plurality of third resist patterns under reduced pressure;

exposing the plurality of third resist patterns by irradiation of light using a second photomask, the light having a photosensitive wavelength region of the second photosensitizer, wherein a third portion where the light is irradiated and a fourth portion where the light is not irradiated are formed in each of the plurality of third resist patterns;

removing one of the third portion and the fourth portion by developing the plurality of third resist patterns to form a plurality of fourth resist patterns;

etching the second conductive layer by using the plurality of fourth resist patterns as a mask to form a plurality of pixel electrodes arranged in a matrix form over the substrate;

removing the plurality of fourth resist patterns on the second conductive layer;

discharging a third composition containing a third photosensitizer on a third conductive layer to form a plurality of fifth resist patterns under reduced pressure;

exposing the plurality of fifth resist patterns by irradiation of light using a third photomask, the

exposing the plurality of first resist patterns with light using a photomask, wherein a first portion where the light is irradiated and a second portion where the light is not irradiated are formed in the first resist patterns; and

removing one of the first portion and the second portion by developing the plurality of first resist patterns to form a plurality of second resist patterns.

20. (Currently Amended) A method for manufacturing a semiconductor device according to claim 19, wherein a viscosity of the composition is at most 100 cp.

21. (Currently Amended) A method for manufacturing a semiconductor device according to claim 19, wherein an amount of the composition discharged at a time is in the range of 10 pl to 70 pl.

22. (Currently Amended) A method for manufacturing a semiconductor device according to claim 19, wherein a wavelength of the light is in the range of 350 nm to 450 nm.

23. (Previously Presented) A method for manufacturing a semiconductor device comprising the steps of:

performing ink jetting on an object to form a plurality of first resist patterns under reduced pressure, wherein each of the plurality of first resist patterns is made of a composition containing a photosensitizer;

exposing the plurality of first resist patterns with light using a photomask ,wherein a first portion where the light is irradiated and a second portion where the light is not irradiated are formed in the first resist patterns; and

removing one of the first portion and the second portion by developing the plurality of first resist patterns to form a plurality of second resist patterns.

24. (Currently Amended) A method for manufacturing a semiconductor device according to claim 23, wherein a viscosity of the composition is at most 100 cp.

25. (Currently Amended) A method for manufacturing a semiconductor device according to claim 23, wherein an amount of the composition discharged at a time is in the range of 10 pl to 70 pl.

26. (Currently Amended) A method for manufacturing a semiconductor device according to claim 23, wherein a wavelength of the light is in the range of 350 nm to 450 nm.

27. (Previously Presented) A method for manufacturing a semiconductor device comprising the steps of:

discharging a composition on an object at pressure in the range of 1×10^2 Pa to 2×10^4 Pa to form a plurality of first resist patterns, the composition containing a photosensitizer;

exposing the plurality of first resist patterns with light using a photomask, wherein a first portion where the light is irradiated and a second portion where the light is not irradiated are formed in the first resist patterns; and

removing one of the first portion and the second portion by developing the plurality of first resist patterns to form a plurality of second resist patterns.

28. (Currently Amended) A method for manufacturing a semiconductor device according to claim 27, wherein a viscosity of the composition is at most 100 cp.

29. (Currently Amended) A method for manufacturing a semiconductor device according to claim 27, wherein an amount of the composition discharged at a time is in the range of 10 pl to 70 pl.

30. (Currently Amended) A method for manufacturing a semiconductor device according to claim 27, wherein a wavelength of the light is in the range of 350 nm to 450 nm.

31. (Previously Presented) A method for manufacturing a semiconductor device comprising the steps of:

performing ink jetting at pressure in the range of 1×10^2 Pa to 2×10^4 Pa to form a plurality of first resist patterns on an object, wherein each of the plurality of first resist patterns is made of a composition containing a photosensitizer;

exposing the plurality of first resist patterns with light using a photomask, wherein a first portion where the light is irradiated and a second portion where the light is not irradiated are formed in the first resist patterns; and

removing one of the first portion and the second portion by developing the plurality of first resist patterns to form a plurality of second resist patterns.

32. (Currently Amended) A method for manufacturing a semiconductor device according to claim 31, wherein a viscosity of the composition is at most 100 cp.

33. (Currently Amended) A method for manufacturing a semiconductor device according to claim 31, wherein an amount of the composition discharged at a time is in the range of 10 pl to 70 pl.

34. (Currently Amended) A method for manufacturing a semiconductor device according to claim 31, wherein a wavelength of the light is in the range of 350 nm to 450 nm.